IN THE CLAIMS:

Please add new claims 25-37, cancel claims 8-24, and amend the claims as follows:

1. (Currently Amended) A method for processing a substrate, comprising:

providing a substrate comprising a ~~first~~ bulk dielectric material disposed on a ~~second~~ patterned dielectric material in an amount sufficient to fill feature definitions of the patterned dielectric material;

polishing the substrate with a first polishing composition and an abrasive-free polishing article until bulk ~~first~~ dielectric material is substantially removed; and

polishing the substrate with a second polishing composition and a fixed-abrasive polishing article to remove residual ~~first~~ bulk dielectric material ~~formed thereon~~ and expose the patterned dielectric material between the feature definitions.

2. (Original) The method of claim 1, wherein the first polishing composition comprises an abrasive-containing polishing composition.

3. (Currently Amended) The method of claim 2, wherein the first polishing composition has a removal rate ratio of ~~first~~ bulk dielectric material to ~~second~~ patterned dielectric material of between about 1:1 and about 5:1.

4. (Currently Amended) The method of claim 1, wherein the second polishing composition has a removal rate ratio of ~~first~~ bulk dielectric material to ~~second~~ patterned dielectric material of about 30:1 or greater.

5. (Original) The method of claim 1, wherein the fixed-abrasive polishing article comprises a high removal rate fixed-abrasive web material.

6. (Original) The method of claim 1, wherein the second polishing composition further contains abrasive particles.

7. (Currently Amended) The method of claim 1, further comprising altering the surface of the fixed-abrasive polishing article with a non-mechanical technique selected from the group of applying heat to the polishing article, chemical etching the polishing article, [[or]] and combinations thereof.

8-24 (Canceled).

25. (New) A method for processing a substrate, comprising:

providing a substrate comprising a material layer, an oxide layer disposed over the material layer, a patterned dielectric material disposed on the oxide layer with feature definitions extending through the three layers, and a bulk dielectric material disposed on the patterned dielectric material in a sufficient amount to fill the feature definitions;

polishing the substrate with a first polishing composition and an abrasive-free polishing article until the bulk dielectric material is substantially removed; and

polishing the substrate with a second polishing composition and a fixed-abrasive polishing article to remove residual bulk dielectric material to expose the patterned dielectric material between the feature definitions.

26. (New) The method of claim 25, wherein the first polishing composition comprises an abrasive-containing polishing composition.

27. (New) The method of claim 26, wherein the first polishing composition has a removal rate ratio of bulk dielectric material to patterned dielectric material of between about 1:1 and about 5:1.

28. (New) The method of claim 25, wherein the second polishing composition has a removal rate ratio of bulk dielectric material to patterned dielectric material of about 30:1 or greater.

29. (New) The method of claim 25, wherein the fixed-abrasive polishing article comprises a high removal rate fixed-abrasive web material.

30. (New) The method of claim 25, wherein the second polishing composition further contains abrasive particles.

31. (New) The method of claim 25, wherein the bulk dielectric material comprises silicon oxide and the patterned dielectric material comprises silicon nitride.

32. (New) A method for processing a substrate, comprising:

providing a substrate comprising a first dielectric material disposed on a second dielectric material, wherein the surface of the first dielectric material has a non-planar topography;

polishing the substrate with a first polishing composition and a fixed-abrasive polishing article to at least planarize the first dielectric material; and then

polishing the substrate with a second polishing composition and an abrasive-free polishing article.

33. (New) The method of claim 32, wherein the first fixed-abrasive polishing article has a first removal rate of the first dielectric material.

34. (New) The method of claim 33, wherein the fixed-abrasive polishing article comprises a high removal rate fixed-abrasive web material.

35. (New) The method of claim 32, wherein the first and second polishing compositions have a removal rate ratio of first dielectric material to second dielectric material of about 30:1 or greater.

36. (New) The method of claim 32, wherein the first dielectric material comprises silicon oxide and the second dielectric material comprises silicon nitride.

37. (New) The method of claim 1, wherein the bulk dielectric material comprises silicon oxide and the patterned dielectric material comprises silicon nitride.